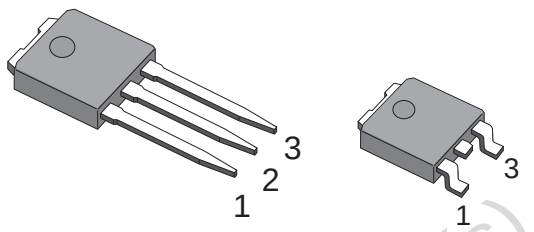
SGS-THOMSON MICROELECTRONICS

STD17N05L
STD17N06L

N - CHANNEL ENHANCEMENT MODE LOW THRESHOLD POWER MOS TRANSISTOR

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STD17N05L	50 V	< 0.085 Ω	17 A
STD17N06L	60 V	< 0.085 Ω	17 A

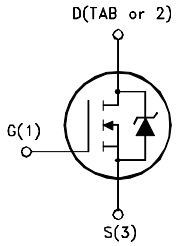
- TYPICAL $R_{DS(on)}$ = 0.065 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW GATE CHARGE
- LOGIC LEVEL COMPATIBLE INPUT
- 175°C OPERATING TEMPERATURE
- APPLICATION ORIENTED CHARACTERIZATION
- THROUGH-HOLE IPAK (TO-251) POWER PACKAGE IN TUBE (SUFFIX "-1")
- SURFACE-MOUNTING DPAK (TO-252) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")



IPAK
TO-251
(Suffix "-1")

DPAK
TO-252
(Suffix "T4")

INTERNAL SCHEMATIC DIAGRAM



APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- REGULATORS
- DC-DC & DC-AC CONVERTERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STD17N05L	STD17N06L	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	50	60	V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	50	60	V
V_{GS}	Gate-source Voltage	± 15		V
I_D	Drain Current (continuous) at T_c = 25 °C	17		A
I_D	Drain Current (continuous) at T_c = 100 °C	12		A
I_{DM}(•)	Drain Current (pulsed)	68		A
P_{tot}	Total Dissipation at T_c = 25 °C	55		W
	Derating Factor	0.37		W/°C
T_{stg}	Storage Temperature	-65 to 175		°C
T_j	Max. Operating Junction Temperature	175		°C

(•) Pulse width limited by safe operating area

Obsolete Product(s) - Obsolete Product(s)

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	2.73	$^oC/W$
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	100	$^oC/W$
$R_{thc\text{-}sink}$	Thermal Resistance Case-sink	Typ	1.5	$^oC/W$
T_l	Maximum Lead Temperature For Soldering Purpose		275	^oC

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	17	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25\ ^oC$, $I_D = I_{AR}$, $V_{DD} = 25$ V)	60	mJ
E_{AR}	Repetitive Avalanche Energy (pulse width limited by T_j max, $\delta < 1\%$)	15	mJ
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive ($T_c = 100\ ^oC$, pulse width limited by T_j max, $\delta < 1\%$)	12	A

ELECTRICAL CHARACTERISTICS ($T_{case} = 25\ ^oC$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\ \mu A$ $V_{GS} = 0$ for **STD17N05L** for **STD17N06L**	 50 60			 V V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	V_{DS} = Max Rating V_{DS} = Max Rating x 0.8 $T_c = 125\ ^oC$			250 1000	µA µA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 15$ V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\ \mu A$	1	1.6	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 5$ V $I_D = 8.5$ A $V_{GS} = 5$ V $I_D = 8.5$ A $T_c = 100\ ^oC$		0.065	0.085 0.17	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10$ V	17			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 8.5$ A	5	12		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25$ V f = 1 MHz $V_{GS} = 0$		700 250 70	1000 350 100	pF pF pF

Obsolete Product(s) - Obsolete Product(s)

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING RESISTIVE LOAD

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 30 V I_D = 8.5 A R_{GS} = 50 Ω V_{GS} = 5 V (see test circuit, figure 3)		60 350	90 500	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	V_{DD} = 40 V I_D = 17 A R_{GS} = 50 Ω V_{GS} = 5 V (see test circuit, figure 5)		130		A/µs
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 40 V I_D = 17 A V_{GS} = 5 V		18 6 9	26	nC nC nC

SWITCHING INDUCTIVE LOAD

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 40 V I_D = 17 A R_{GS} = 50 Ω V_{GS} = 5 V (see test circuit, figure 5)		70 100 180	100 150 260	ns ns ns

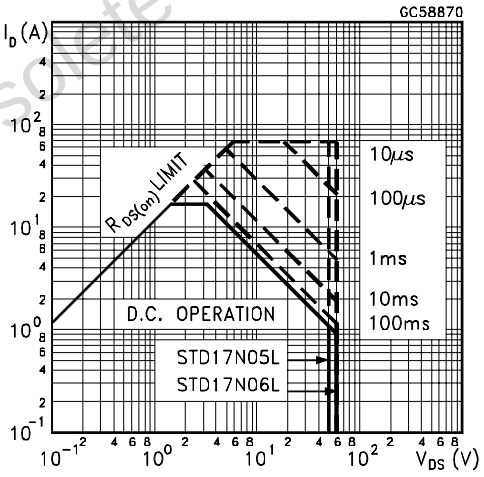
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				17 68	A A
V_{SD} (*)	Forward On Voltage	I_{SD} = 17 A V_{GS} = 0			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 17 A di/dt = 100 A/µs V_{DD} = 30 V T_j = 150 °C (see test circuit, figure 5)		65 0.13 4		ns µC A

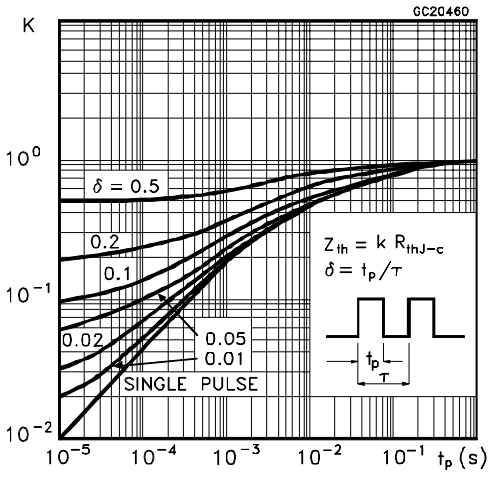
(*) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

(•) Pulse width limited by safe operating area

Safe Operating Area

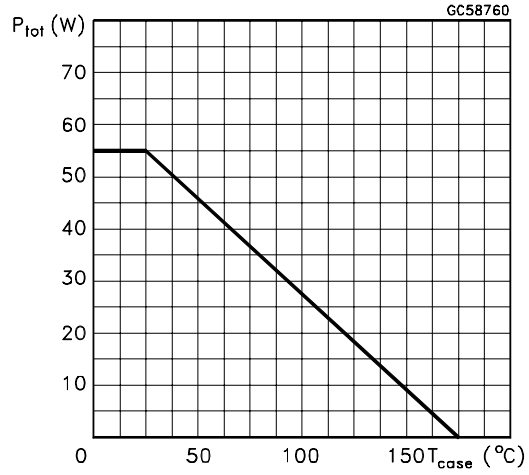


Thermal Impedance

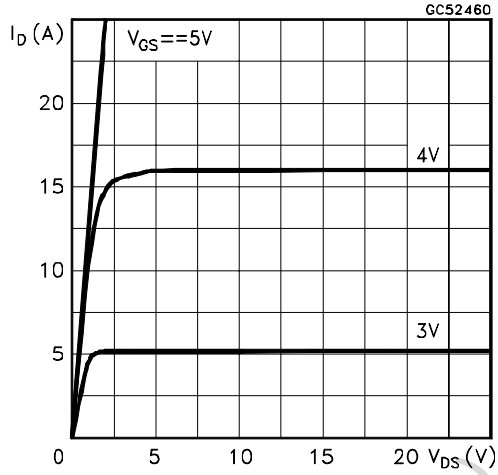


Obsolete Product(s) - Obsolete Product(s)

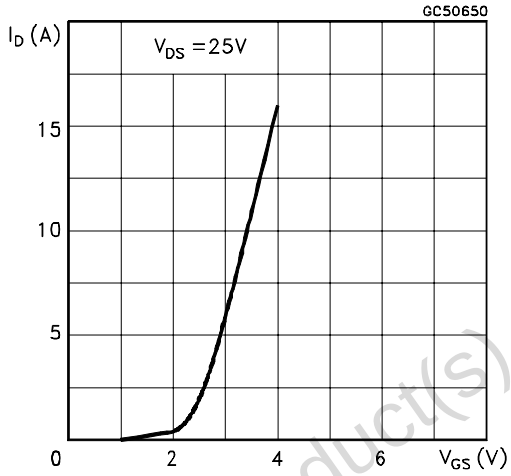
Derating Curve



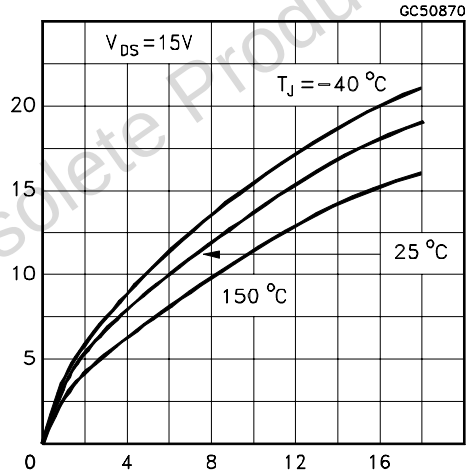
Output Characteristics



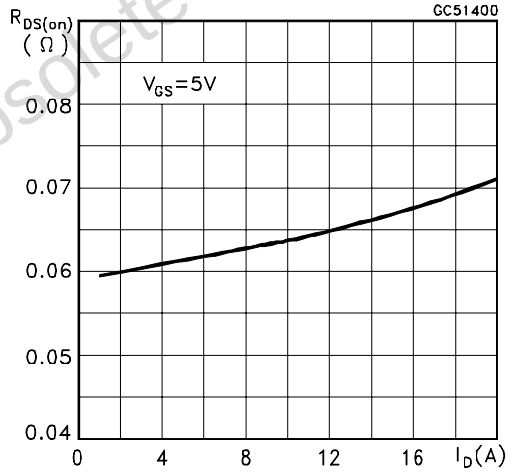
Transfer Characteristics



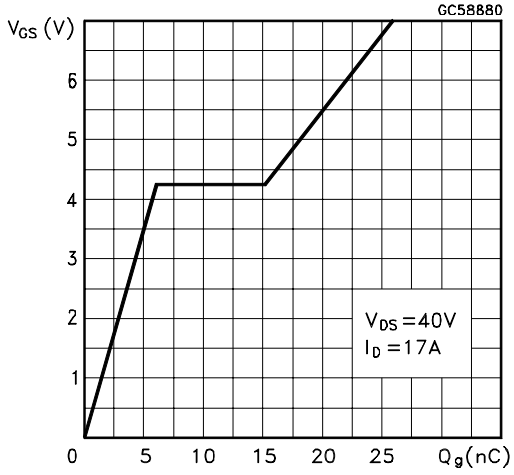
Transconductance



Static Drain-source On Resistance

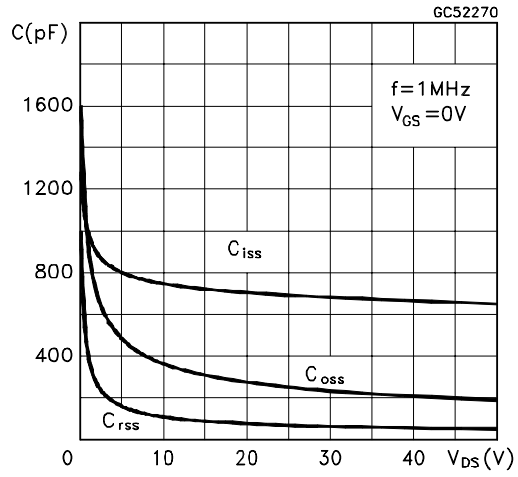


Gate Charge vs Gate-source Voltage

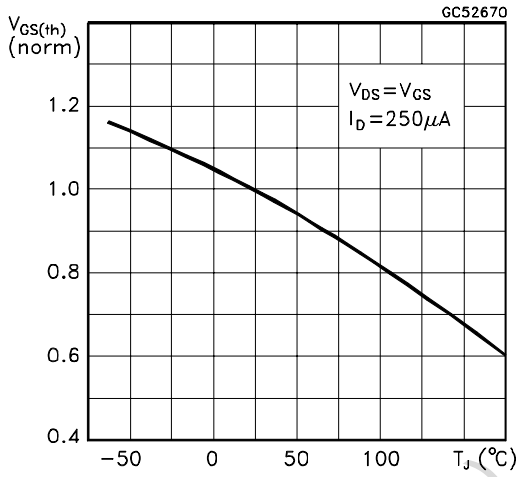


Obsolete Product(s) - Obsolete Product(s)

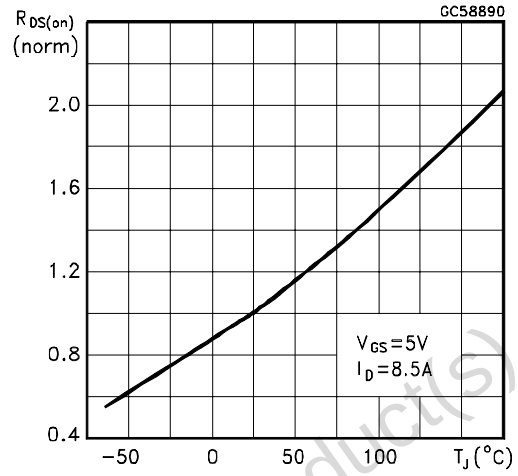
Capacitance Variations



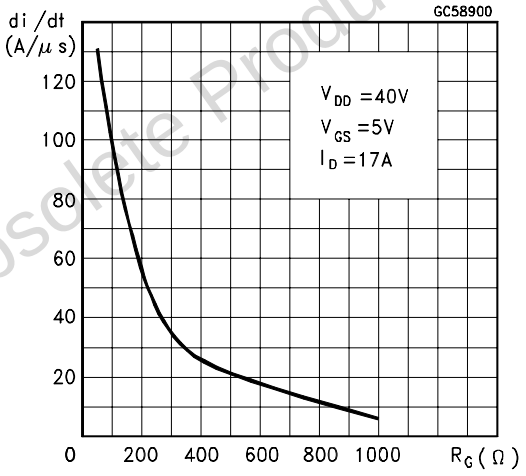
Normalized Gate Threshold Voltage vs Temperature



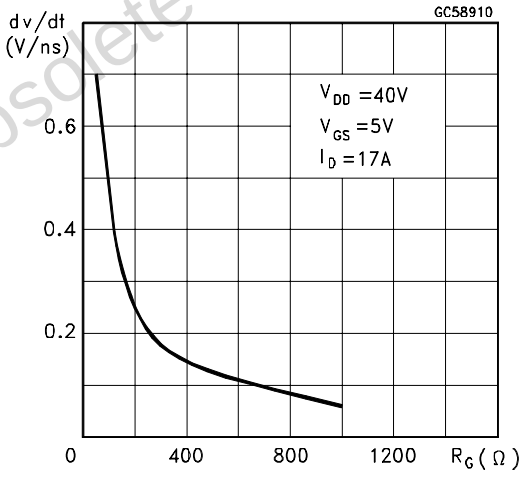
Normalized On Resistance vs Temperature



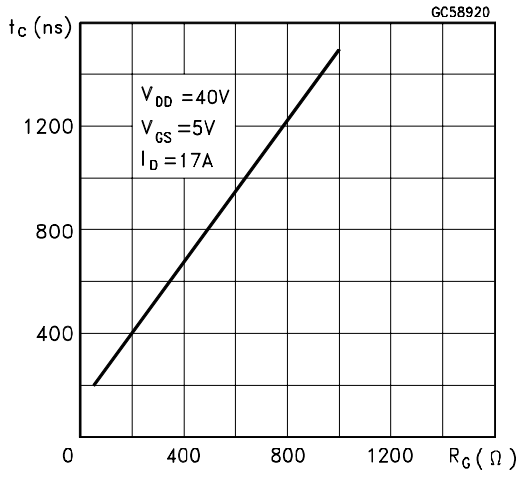
Turn-on Current Slope



Turn-off Drain-source Voltage Slope

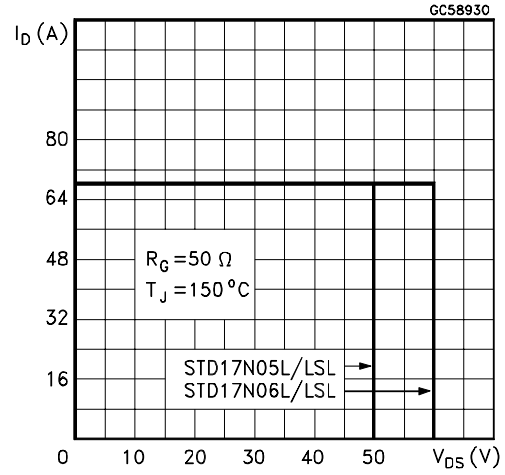


Cross-over Time

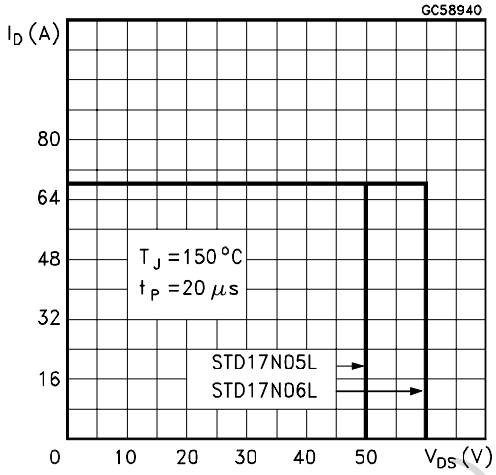


Obsolete Product(s) - Obsolete Product(s)

Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

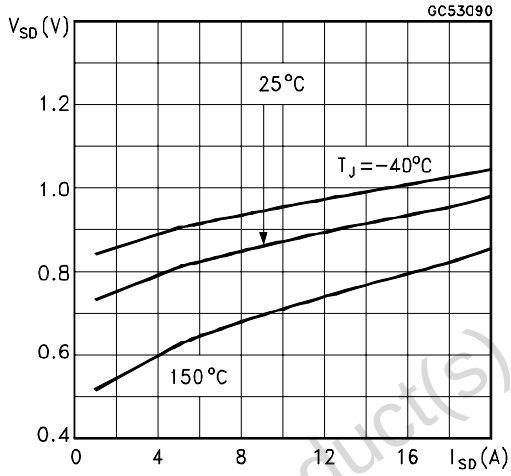


Fig. 1: Unclamped Inductive Load Test Circuits

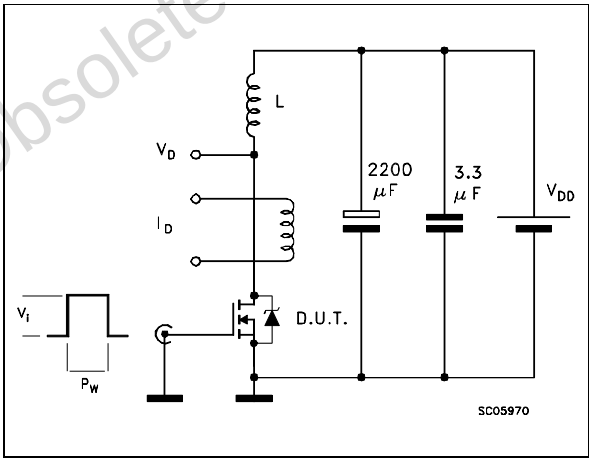
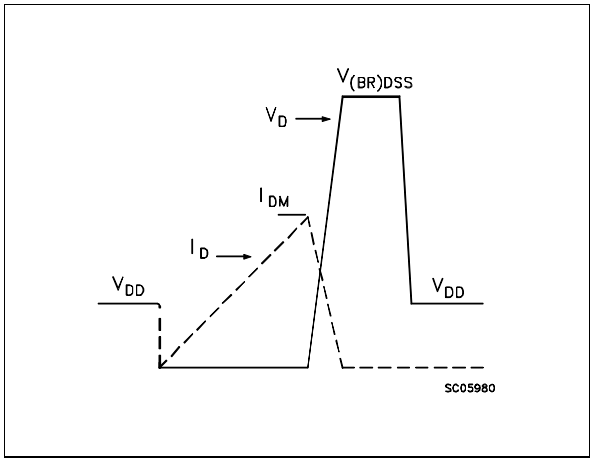


Fig. 2: Unclamped Inductive Waveforms



Obsolete Product(s) - Obsolete Product(s)

Fig. 3: Switching Times Test Circuits For Resistive Load

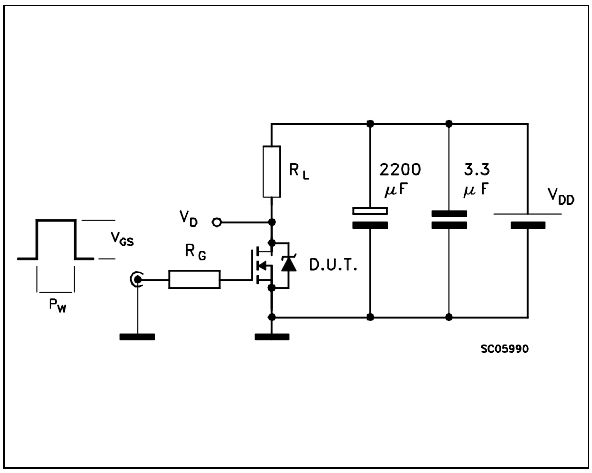


Fig. 4: Gate Charge Test Circuit

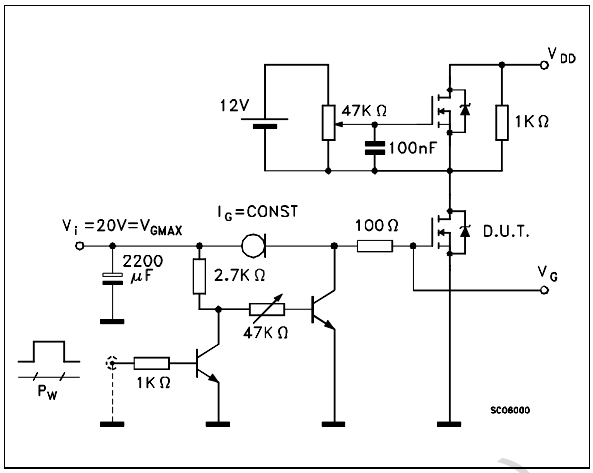
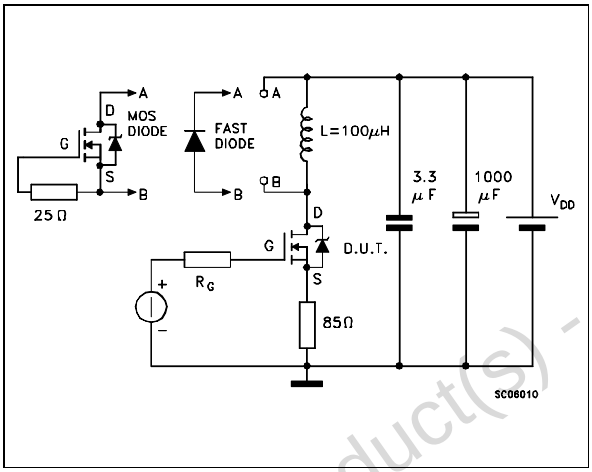


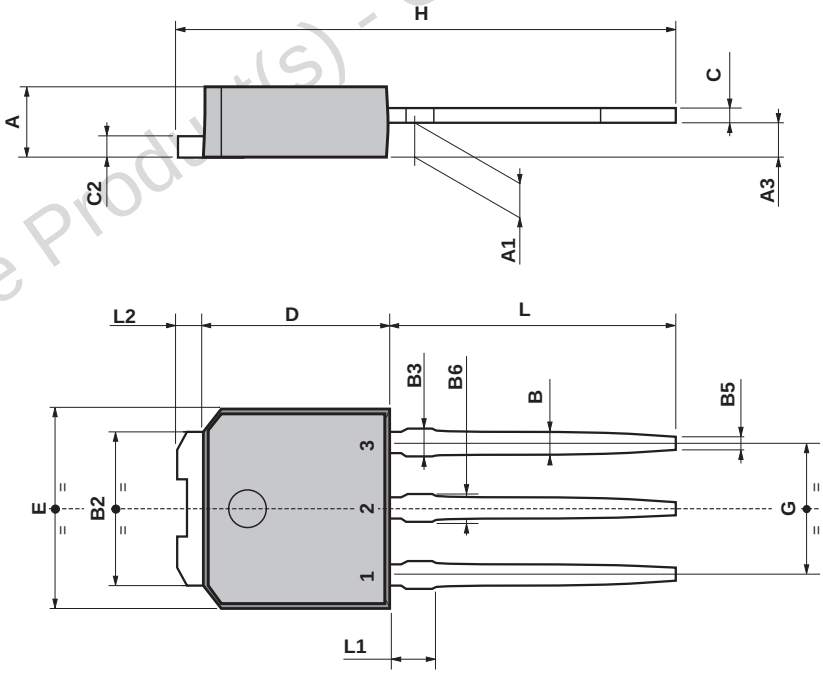
Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



Obsolete Product(s) - Obsolete Product(s)

TO-251 (IPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039

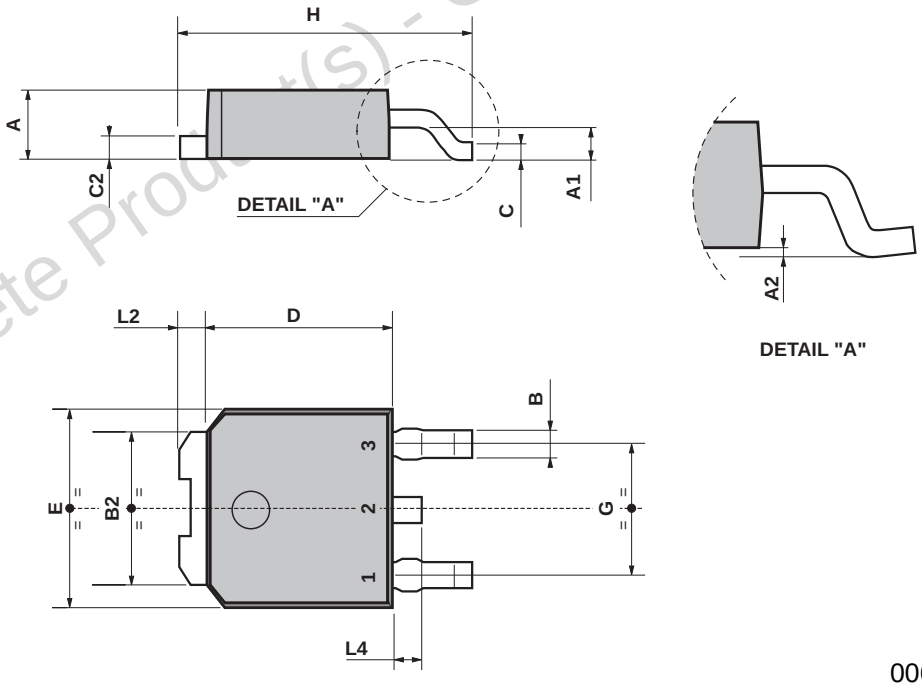


0068771-E

Obsolete Product(s) - Obsolete Product(s)

TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L2		0.8			0.031	
L4	0.6		1	0.023		0.039



0068772-B

Obsolete Product(s) - Obsolete Product(s)

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